Abstracts

A High Power 50GHz DDR IMPATT Oscillator with Low Side Band Noise

Y. Hirachi, Y. Toyama, Y. Fukukawa and Y. Tokumitsu. "A High Power 50GHz DDR IMPATT Oscillator with Low Side Band Noise." 1976 MTT-S International Microwave Symposium Digest of Technical Papers 76.1 (1976 [MWSYM]): 36-39.

Low-frequency instabilities in millimeter-wave Double-Drift-Region (DDR) IMPATT diodes are investigated and the oscillator circuit which suppresses low-frequency instabilities is developed. DDR IMPATT mounted in this circuit exhibited output powers 1.6W at 55.5 GHz with 11.5 percent efficiencies.

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